A Cagri Ulusoy

List of Publications by Year
in descending order

48 papers	795 citations	759233 12 h-index	610901 24 g-index
48 all docs	48 docs citations	48 times ranked	864 citing authors

#	Article	IF	Citations
1	Active BALUN with 40 GHz bandwidth at 257 GHz in 130 nm SiGe:C. , 2022, , .		1
2	A 220â€“261 GHz Frequency Multiplier Chain (Ã— 18) With 8-dBm Peak Output Power in 130-nm SiGe. IEEE Microwave and Wireless Components Letters, 2022, 32, 895-898.	3.2	5
3	A 225â€“265 GHz I-Q Receiver in 130-nm SiGe BiCMOS for FMCW Radar Applications. IEEE Microwave and Wireless Components Letters, 2022, 32, 899-902.	3.2	4
4	A D-Band Power Amplifier with 15 dBm P_{sat} in 0.13 Âµm SiGe BiCMOS Technology. , 2022, , .		4
5	A Differential D-Band Low-Noise Amplifier in 0.13 Î¼m SiGe. IEEE Microwave and Wireless Components Letters, 2022, 32, 979-982.	3.2	3
6	DC-to-Ka-band Broadband Chip-to-Chip Interconnect Using Aerosol Jet Printing. , 2021, , .		1
7	A Reflection Type Phase Shifter for Reconfigurable Reflectarrays at 240 GHz. , 2021, , .		4
8	A Linear and Efficient Power Amplifier Supporting Wideband 64-QAM for 5G Applications from 26 to 30 GHz in SiGe:C BiCMOS. , 2021, , .		5
9	A High Sensitivity RF Energy Harvester for Diverse Environments. , 2021, , .		2
10	A Compact W-Band Frequency Tripler Using Single-Balanced Topology. IEEE Microwave and Wireless Components Letters, 2020, 30, 806-809.	3.2	11
11	A 28-/60-GHz Band-Switchable Bidirectional Amplifier for Reconfigurable mm-Wave Transceivers. IEEE Transactions on Microwave Theory and Techniques, 2020, 68, 3197-3205.	4.6	12
12	A 20â€“60 GHz Ultra-Wideband SPDT Switch for Multi-Band Transceivers. , 2020, , .		6
13	Aerosol Jetting for Multifunctional Additive Manufacturing. , 2020, , 437-445.		0
14	A W-Band SiGe Transceiver with Built-in Self-Test. , 2019, , .		2
15	AKa/VBand-Switchable LNA With 2.8/3.4 dB Noise Figure. IEEE Microwave and Wireless Components Letters, 2019, 29, 662-664.	3.2	26
16	A 28/60 GHz Dual-band Power Amplifier. , 2019, , .		5
17	A Compact V-Band Upconversion Mixer With â^’1.4-dBm OP1dB in SiGe HBT Technology. IEEE Microwave and Wireless Components Letters, 2019, 29, 276-278.	3.2	12
18	UHF Rectenna for Implanted and Free Space Communications. , 2019, , .		1

#	Article	IF	Citations
19	SiRF 2020 [IEEE Radio & Wireless Week 2020]. IEEE Microwave Magazine, 2019, 20, 26-26.	0.8	0
20	Harmonic Tuning of Stacked SiGe Power Amplifiers Using Active Load Pull. IEEE Microwave and Wireless Components Letters, 2018, 28, 245-247.	3.2	6
21	A 0.87-pJ/b 115-Gb/s $2^{ext {7}}$ -1 PRBS Generator in 130-nm SiGe:C BiCMOS Technology. IEEE Solid-State Circuits Letters, 2018, 1, 42-45.	2.0	4
22	Aerosol-Printed Highly Conductive Ag Transmission Lines for Flexible Electronic Devices. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2018, 8, 1838-1844.	2.5	27
23	Wideband 240-GHz Transmitter and Receiver in BiCMOS Technology With 25-Gbit/s Data Rate. IEEE Journal of Solid-State Circuits, 2018, 53, 2532-2542.	5.4	87
24	A 0.3â€“15 GHz SiGe LNA With >1 THz Gain-Bandwidth Product. IEEE Microwave and Wireless Components Letters, 2017, 27, 380-382.	3.2	11
25	Encapsulated Organic Package Technology for Wideband Integration of Heterogeneous MMICs. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 438-448.	4.6	11
26	A DC-90-GHz 4- $V_{mathrm{ pp}}$ Modulator Driver in a 0.13- $mu ext{m}$ SiGe:C BiCMOS Process. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 5192-5202.	4.6	19
27	A 220â€“275 GHz Direct-Conversion Receiver in 130-nm SiGe:C BiCMOS Technology. IEEE Microwave and Wireless Components Letters, 2017, 27, 675-677.	3.2	29
28	216â€“256 GHz fully differential frequency multiplier-by-8 chain with 0 dBm output power. , 2017, , .		15
29	Ultra wideband 3D interconnects using aerosol jet printing up to 110 GHz. , 2017, , .		10
30	Ultra wideband 3D interconnects using aerosol jet printing up to 110 GHz. , 2017, , .		3
31	A Monolithically Integrated Segmented Linear Driver and Modulator in EPIC 0.25- mu m SiGe:C BiCMOS Platform. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 4561-4572.	4.6	40
32	Inverse classâ€‹<scp>F</scp><scp>X</scp>â€‹band <scp>S</scp>i<scp>G</scp>e <scp>HBT</scp> power amplifier with 44% <scp>PAE</scp> and 24.5 d<scp>B</scp>m peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	1.4	1
33	A Reactively Matched 1.0â€“11.5 GHz Hybrid Packaged GaN High Power Amplifier. IEEE Microwave and Wireless Components Letters, 2015, 25, 811-813.	3.2	6
34	A 5.4W X-band gallium nitride (GaN) power amplifier in an encapsulated organic package. , 2015, , .		10
35	A Comparison of the Degradation in RF Performance Due to Device Interconnects in Advanced SiGe HBT and CMOS Technologies. IEEE Transactions on Electron Devices, 2015, 62, 1803-1810.	3.0	50
36	High-performance W-band LNA and SPDT switch in 0.13µm SiGe HBT technology. , 2015, , .		0

#	Article	IF	Citations
37	An investigation of f<inf>T</inf> and f<inf>max</inf> degradation due to device interconnects in 0.5 THz SiGe HBT technology. , 2014, , .		3
38	A feasibility study of flip-chip packaged gallium nitride HEMTs on organic substrates for wideband RF amplifier applications. , 2014, , .		8
39	A low-cost, encapsulated flip-chip package on organic substrate for wideband gallium nitride (GaN) hybrid amplifiers. , 2014, , .		8
40	A high-power, low-loss W-band SPDT switch using SiGe PIN diodes. , 2014, , .		35
41	A Low-Loss and High Isolation D-Band SPDT Switch Utilizing Deep-Saturated SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2014, 24, 400-402.	3.2	37
42	On the Analysis and Design of Low-Loss Single-Pole Double-Throw W-Band Switches Utilizing Saturated SiGe HBTs. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2755-2767.	4.6	132
43	Packaging a W-Band Integrated Module With an Optimized Flip-Chip Interconnect on an Organic Substrate. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 64-72.	4.6	37
44	A switchable-core SiGe HBT low-noise amplifier for millimeter-wave radiometer applications. , 2014, , .		2
45	A 94 GHz, 1.4 dB Insertion Loss Single-Pole Double-Throw Switch Using Reverse-Saturated SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2014, 24, 56-58.	3.2	37
46	Characterization of a low-loss and wide-band (DC to 170 GHz) flip-chip interconnect on an organic substrate. , 2014, , .		15
47	D-Band characterization of co-planar wave guide and microstrip transmission lines on liquid crystal polymer. , 2013, , .		24
48	A 60 to 77 GHz Switchable LNA in an RF-MEMS Embedded BiCMOS Technology. IEEE Microwave and Wireless Components Letters, 2012, 22, 430-432.	3.2	24